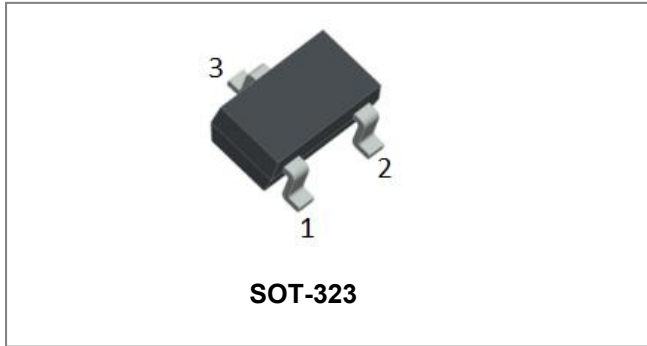


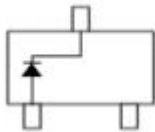
## BAS19W-BAS21W SURFACE MOUNT FAST SWITCHING DIODE



### Features

- High Conductance
- Fast Switching
- Surface Mount Package Ideally Suited for Automatic Insertion
- For General Purpose and Switching
- Plastic Material - UL Recognition Flammability Classification 94V-0
- This is a Pb - Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

### Schematic & Pin Configuration



### Mechanical Characteristics

- Case: SOT-323, Molded Plastic
- Terminals: Plated leads Solderable per MIL-STD-202, Method 208
- Weight: 0.006g
- Mounting Position: Any

### Maximum Ratings@T<sub>A</sub>=25°C unless otherwise specified

Characteristic	Symbol	BAS19W	BAS20W	BAS21W	Units
Non-Repetitive Peak Reverse Voltage	V <sub>RM</sub>	120	200	250	V
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V <sub>RRM</sub> V <sub>RWM</sub> V <sub>R</sub>	100	150	200	V
RMS Reverse Voltage(Note 1)	V <sub>R(RMS)</sub>	70	105	140	V
Forward Continuous Current (Note 1)	I <sub>FM</sub>	400			mA
Average Rectified Output Current(Note 1)	I <sub>o</sub>	200			mA
Non-Repetitive Peak Forward Surge Current @t=1us	I <sub>FSM</sub>	2.5			A
Power Dissipation	P <sub>D</sub>	200			mW
Thermal Resistance, Junction to Ambient(Note 1)	R <sub>θJA</sub>	625			°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-65 to +150			°C

**Electrical Characteristics @ $T_A=25^\circ\text{C}$  unless otherwise specified**

Characteristic	Symbol	Min	Max	Units	Test Condition
Forward Voltage*	$V_F$	-	1.00 1.25	V	@ $I_F=100\text{mA}$ @ $I_F=200\text{mA}$
Reverse Leakage Current*	$I_R$	-	100	nA	@Rated DC Blocking Voltage
Capacitance between terminals	$C_T$	-	5	pF	$V_R=0\text{V}$ , $f=1.0\text{MHz}$
Reverse Recovery Time	$t_{rr}$	-	50	ns	$I_F=I_R=30\text{mA}$ , $I_{RR}=0.1 \times I_R$ , $R_L=100\Omega$

\* Pulse width < 300  $\mu\text{s}$ , duty cycle < 2%  
Note: 1. Device mounted on fiberglass substrate 40x40x1.5mm

**Ratings and Characteristics Curves**

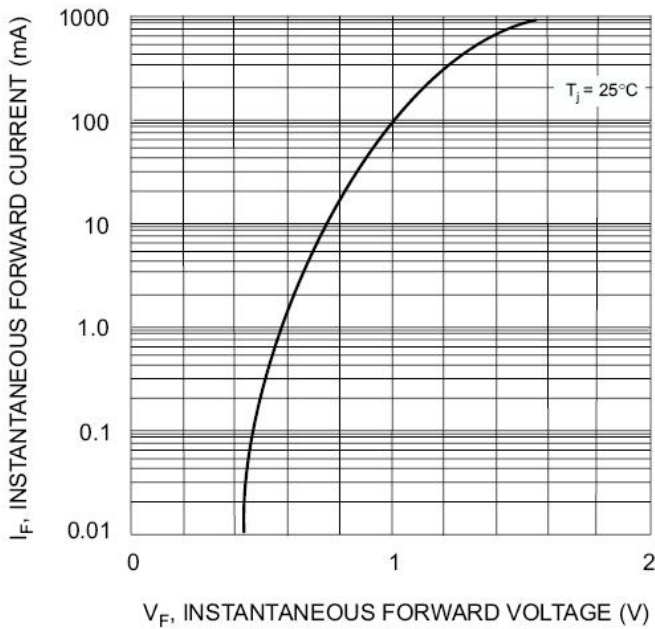


Fig. 1 Forward Characteristics

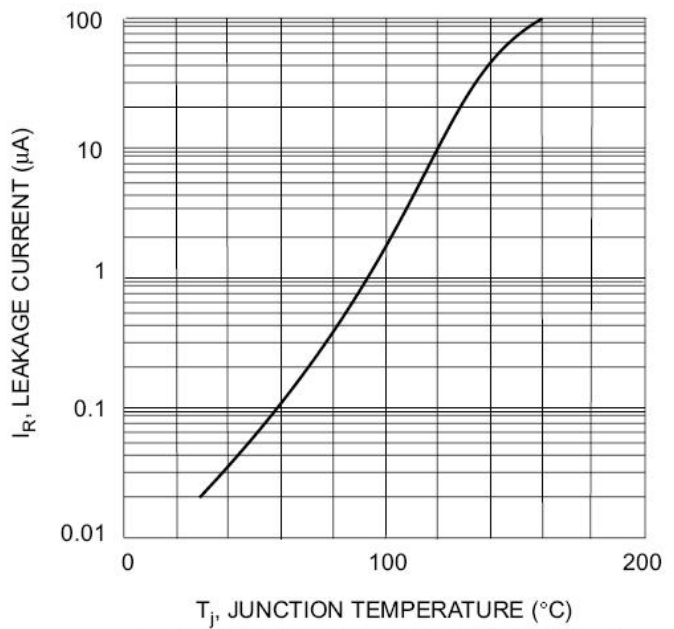


Fig. 2 Leakage Current vs Junction Temperature

**Ordering Information**

Device	Package	Shipping
BAS19W-BAS21W	SOT-323 (Pb-Free)	3000pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

**Marking Diagram**

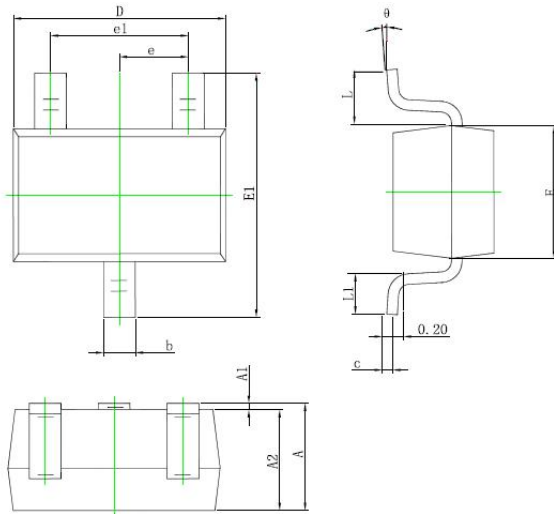
Marking before 16441(Date Code)

Part Number	Device Marking Code
BAS19W	A8
BAS20W	A80
BAS21W	A82

Marking from 16441(Date Code)

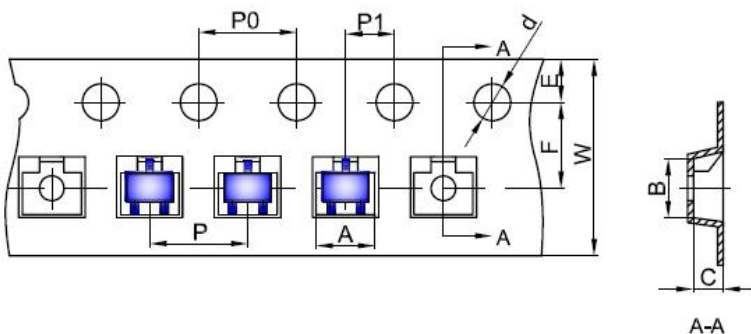
Part Number	Device Marking Code
BAS19W	KA8
BAS20W	KT2
BAS21W	KT3

**Mechanical Dimensions SOT-323**



SYMBOL	Millimeters		Inches	
	MIN.	MAX.	MIN.	MAX.
A	0.900	1.100	0.035	0.043
A1	0.000	0.100	0.000	0.004
A2	0.900	1.000	0.035	0.039
b	0.200	0.400	0.008	0.016
c	0.080	0.150	0.003	0.006
D	2.000	2.200	0.079	0.087
E	1.150	1.350	0.045	0.053
E1	2.150	2.450	0.085	0.096
e	0.650 TYP.		0.026 TYP.	
e1	1.200	1.400	0.047	0.055
L	0.525 REF.		0.021 REF.	
L1	0.260	0.460	0.010	0.018
θ	0°	8°	0°	8°

**Carrier Tape Specification SOT-323**



SYMBOL	Millimeters	
	Min.	Max.
A	2.20	2.30
B	2.50	2.60
C	1.14	1.24
d	1.45	1.65
E	1.65	1.85
F	3.40	3.60
P	3.90	4.10
P0	3.90	4.10
P1	1.90	2.10
W	7.90	8.30



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